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4. (Currently amended) The method of claim 3 wherein forming a barrier layer comprises forming a barrier layer that is from about ~~150~~^{angstroms}₅₀ to about ~~350~~₃₀₀ angstroms in thickness.
5. (Original) The method of claim 1 wherein forming a sacrificial layer on a hard mask layer disposed on a substrate comprises forming a sacrificial layer disposed on a hard mask layer that is disposed on a dielectric layer.
6. (Original) The method of claim 1 wherein forming a sacrificial layer on a hard mask layer disposed on a substrate comprises forming a sacrificial layer disposed on a hard mask layer that is disposed on a low k dielectric layer.
7. (Original) The method of claim 1 wherein simultaneously removing the metal layer and the sacrificial layer comprises simultaneously removing the metal layer and the sacrificial layer at a removal rate that is at least about 10 times faster than a removal rate of the hard mask layer.
8. (Original) The method of claim 7 wherein simultaneously removing the metal layer and the sacrificial layer at a first removal rate that is at least about 10 times faster than the removal rate of the hard mask layer comprises simultaneously removing the metal layer and the sacrificial layer at a removal rate that is from about 50 to about 100 times faster than a removal rate of the hard mask layer.